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Editors: Thomas O. Sedgwick, Thomas E. Seidel and Bor-Yeu Tsaur

Index

[More information](#)

481

Author Index

- Adekoya, W.O., 115
 Ahmed, H., 65, 123
 Alvi, N.S., 73, 241
 Araujo, C., 225
 Avau, D., 217

 Baiocchi, F.A., 23
 Bao, X.M., 173
 Bauman, S.G., 73
 Blackstone, S., 157, 297
 Boerma, D.O., 351
 Broadbent, E.K., 279
 Bulat, E.S., 271

 Calder, I.D., 251
 Capodilupo, R.A., 321
 Carpenter, R.W., 139
 Cheung, A.W., 241
 Cheung, N.W., 383
 Chu, P.K., 383
 Chu, W.K., 31
 Cohen, S.A., 153, 327
 Cowern, N.E.B., 65
 Culbertson, R.J., 37
 Cummings, K.D., 375

 Davis, R.F., 157, 165
 d'Heurle, F.M., 261
 Dietrich, H.B., 423
 Ditchek, B.M., 271
 Duh, K.H.G., 417

 Edmond, J.A., 157
 Ellington, M.B., 93

 Fathy, D., 31
 Fonstad, C.G., 403

 Gat, A., 209, 233
 Gelpy, J.C., 199, 225, 321
 Gibbons, J.F., 15, 305
 Gibson, J.M., 351
 Godfrey, D.J., 65
 Gregory, R.B., 145, 181
 Gronet, C.M., 305
 Gwilliam, R., 391

 Hardeman, R.W., 313
 Hasko, D.G., 65
 Ho, C.C., 225
 Hodge, A.M., 313
 Hodgson, R.T., 261
 Hodul, D.T., 131

 Hopkins, C.G., 73
 Hoyt, J.L., 15
 Huang, J., 57
 Hull, R., 93, 361
 Hwang, H.L., 431
 Hwang, J.C.M., 417

 Jaccodine, R.J., 57
 Jacobson, D.C., 93, 351, 361
 Jensen, H.R., 83
 Joy, D.C., 93

 Kalish, R., 327
 Kamgar, A., 23
 Kazior, T.E., 397
 Kelly, J.C., 139
 Kepler, N.J., 383
 Kim, H.J., 157, 165
 Kirillov, D., 131
 Knoell, R.V., 93
 Kong, W.M., 417
 Krause, S.J., 145
 Krusius, J.P., 341
 Ku, Y.H., 241
 Kwong, D.L., 73, 241
 Kwor, R., 225

 Lam, C.S., 403
 Leavitt, J.A., 145
 Lester, L.F., 417
 Lever, R.F., 49
 Licoppe, C., 369
 Liliental-Weber, Z., 139
 Lin, J.L., 431
 Liu, C.E., 173
 Lu, Z.H., 31
 Lue, J.T., 431

 Madsen, L.D., 251
 Maes, H.E., 217
 Maher, D.M., 93
 Manion, M.L., 441
 Maszara, W., 107
 McIntyre Jr., L.C., 145
 McMahon, R.A., 65, 123
 McPhail, D.S., 65
 McVittie, J., 233
 Mercier, J.S., 251
 Meriadec, C., 269
 Mertens, P., 217
 Michel, A.E., 3
 Molnar, B., 423
 Morehead, F.F., 49
 Morgan, A.E., 279

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Index

[More information](#)

482

- Muller, J.C., 115
 Mun, J., 409
 Myers, E., 107
 Narayan, J., 107
 Nguyen, T.N., 327
 Nissim, Y.I., 369
 Nulman, J., 233, 341
 Numan, M.Z., 31
 Paulson, W.M., 145, 181
 Pearton, S.J., 351, 361, 375
 Pedulli, L., 115
 Pennycook, S.J., 37
 Pettibone, D.W., 209
 Pickering, C., 313
 Pidduck, A.J., 313
 Plummer, J.D., 333
 Poate, J.M., 351, 361
 Powell, R.A., 131, 441
 Ransom, C.M., 153
 Reader, A.H., 279
 Reed, M.L., 333
 Renteln, P., 341
 Rozgonyi, G.A., 107
 Ryu, J., 165
 Sadana, D.K., 107
 Santiago, J.J., 289, 297
 Sealy, B.J., 391
 Sedgwick, T.O., 153
 Seerveld, J.L., 145
 Setton, M., 297
 Shah, N., 233
 Shahid, M.A., 391
 Sharif, N., 233
 Shatas, S., 271
 Sheets, R.E., 191
 Siegal, M., 289
 Siffert, P., 115
 Simard-Normandin, M., 83
 Smith, J.W., 199
 Smith, P.M., 417
 Stobbs, W.M., 65
 Stoss, P., 145
 Stump, P.O., 199, 321
 Sturm, J.C., 305
 Suarez, J.R., 209
 Sullivan, M.A., 271
 Tabasky, M., 271
 Tabatabaie-Alavi, K., 397
 Tanielian, M., 297
 Timans, P.J., 123
 Ting, C.Y., 261
 Ueng, H.Y., 431
 Van der Spiegel, J., 289, 297
 Vella-Coleiro, G.P., 375
 Wei, C.S., 297
 Weinberg, Z.A., 327
 Williams, J.S., 351, 361
 Williams, K.F., 305
 Wilson, S.R., 145, 181
 Wood, D., 409
 Wortman, J.J., 31, 107
 Wouters, D., 217
 Yallup, K.J., 65
 Yang, M.H., 431
 Young, J.F., 83
 Yu, T-H., 417
 Zhang, X.Y., 173
 Zheng, X.Q., 173

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Index

[More information](#)

483

Subject Index

- activation
 - dopant, 3, 23, 31, 57, 65, 115, 217, 241, 251, 361, 375, 391, 403, 417, 431, 447
 - temperature dependence, 23, 375
 - uniformity, 375, 397, 417
- amorphous layers, 37, 65, 93, 107, 123, 131, 241
- annealing equipment, 181
- bilayers, 279, 297
- Boltzmann-Matano analysis, 49
- borophosphosilicate glass, 251
- characterization
 - non-destructive, 83
 - defect, 115, 153
 - energy spectra of dislocations, 173
- clustering, 3, 23, 31
- compound semiconductors, 460
- contact resistance, 271
- copper indium disulfide, 431
- damage removal, 93, 361
- deactivation, 23
- deep level transient spectroscopy, 153, 173
- defects and microstructure, 31, 37, 65, 93, 107, 241, 465
- spanning "hairpin" dislocations, 107
- device applications
 - silicon, 466
 - compound semiconductors, 469
- diodes, 153, 225
- differential Hall measurements, 225
- diffusion
 - anomalous, 3, 49
 - enhanced, 3, 37, 65, 73
 - ion implanted impurities, 447
 - As, 3, 15, 73, 241
 - B, 3, 15, 65
 - P, 49, 241
 - Sb, 37
 - in silicides, 261
 - modelling, 3, 15, 49, 472
 - transient, 3, 15, 37
- dielectrics, 341, 458
- electron mobility, 423
- ellipsometry, 313, 321
- emissivity, 191, 209
- encapsulation, 351, 391
- equipment, 181, 471
- feedback control, of
 - temperature, 321
- field effect transistors, 397, 409, 417
- gallium arsenide, 361, 369, 375, 383, 391, 397, 460
- diffused contacts, 351, 383
- field effect transistors, 397, 409, 417
- glass fusion and reflow, 233, 251
- growth rate
 - amorphous layer, 123, 131, 369
 - enhanced palladium silicide, 65
 - oxides, 313, 321
- indium gallium arsenide, 403
- indium phosphide, 423
- interface
 - silicide/silicon, 73
 - silicon/silicon dioxide traps, 333
- infrared attenuated total reflection, 83
- interstitials, trapped, 37
- insulator buried layer, 139
- ion implanted impurities
 - activation and deactivation, 3, 23, 31, 57, 65, 145, 447
 - characterization of B and BF^+_2 , 83
 - heavy doping, 23, 31, 145
 - in silicon carbide, 157, 165
 - metastable, 23, 31
 - Be in GaAs, 403
 - projected range defects, 37
 - Se in GaAs, 391
- kinetics
 - amorphous GaAs regrowth, 369
 - arsenic clustering, 23
 - interface state annealing, 333
- laser annealing, 173
- leakage current, 225
- limited reaction processing, 305
- majority carrier traps, 153

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Editors: Thomas O. Sedgwick, Thomas E. Seidel and Bor-Yeu Tsaur

Index

[More information](#)

484

- metals, 457
- miscellaneous applications, 470
- multi-step anneal, 417
- nitridation, 341
- nucleation, 261, 289
- ohmic contacts, 383
- optical pyrometer, 191, 199, 209
- oxidation, 313, 321, 341
- oxygen implanted silicon, 139
- oxynitrides, 341
- p-n Junctions, 165
- phase transformation, 289
- phosphosilicate glass, 233
- photoconductance
 - scanning microwave, 375
- photoelectron spectroscopy, 313
- polycrystalline silicon, 145, 452
- preamorphization, 107, 241
- processing equipment, 181, 471
- process control, 191, 199, 209, 321, 471
- pulsed electron beam annealing, 431
- pyrometer, 191, 199, 209, 321
- radiation sources, 181, 217
- rapid thermal processing
 - comparison
 - of equipment, 181
 - of radiation sources, 217
- Raman scattering, 131
- reflow, 251
- recrystallization, 93, 115, 123
- Reviews of Rapid Thermal Processing, 446
- self aligned gate transistor, 409
- silicidation, 271
- silicide, 261, 454
 - cobalt, 271
 - growth rate, 261
 - enhanced, 73
 - kinetics of growth, 261
 - palladium, 65
 - selective formation, 271
 - ternary, 297
 - titanium, 241, 279, 297, 409
 - tungsten, 289, 297
- silicon carbide, 157, 165
- silicon epitaxy, 305
- silicon dioxide, 458
 - annealing, 327
 - breakdown, 327
 - electron trapping, 327
 - growth, 305, 321, 327
- silicon nitride, 391
- silicon-on-sapphire, 123
- slip formation, 351
- solid phase epitaxial growth, 107, 369
- solubility, As in Si, 15
- temperature measurement and control, 191, 199, 209, 321
- thermocouple, 191, 199, 209
- time resolved reflectivity, 123, 369
- titanium nitride, 279
- transmission electron microscopy, 31, 37, 57, 65, 93, 107, 115, 139, 145, 217, 241, 279, 341, 361, 391, 465
 - cross-section, 37, 65, 93, 107
- reverse annealing, 57
- vacuum annealing, 15
- very low temperature annealing, 107
- water-wall arc lamp, 321